Jing Lu

List of Publications by Year
in descending order

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153	7,672	38660 50	60497 81
papers	citations	h-index	g-index

155	155	155	7390
all docs	docs citations	times ranked	citing authors

#	ARTICLE	IF	CITATIONS
1	Device performance and strain effect of sub-5 nm monolayer InP transistors. Journal of Materials Chemistry C, 2022, 10, 2223-2235.	2.7	10
2	Giant tunnelling electroresistance through 2D sliding ferroelectric materials. Materials Horizons, 2022, 9, 1422-1430.	6.4	23
3	Device simulation of GeSe homojunction and vdW GeSe/GeTe heterojunction TFETs for high-performance application. Journal of Computational Electronics, 2022, 21, 401-410.	1.3	3
4	Scaling Behavior of Magnetoresistance with the Layer Number in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:msub><mml:mrow><mml:mi>Cr</mml:mi><mml:mi mathvariant="normal">I</mml:mi></mml:mrow><mml:mn>3</mml:mn></mml:msub></mml:math> Magnetic Tunnel Junctions. Physical Review Applied, 2022, 17, .	1.5	10
5	Oligonucleotide Discrimination Enabled by Tannic Acid-Coordinated Film-Coated Solid-State Nanopores. Langmuir, 2022, 38, 6443-6453.	1.6	9
6	Performance Limit of Ultrathin GaAs Transistors. ACS Applied Materials & Interfaces, 2022, 14, 23597-23609.	4.0	22
7	Correlating the electronic structures of metallic/semiconducting MoTe2 interface to its atomic structures. National Science Review, 2021, 8, nwaa087.	4.6	5
8	Reaction Mechanism and Structural Evolution of Fluorographite Cathodes in Solidâ€State K/Na/Li Batteries. Advanced Materials, 2021, 33, e2006118.	11.1	44
9	Highâ€Performance Spin Filters and Spin Field Effect Transistors Based on Bilayer VSe₂. Advanced Theory and Simulations, 2021, 4, 2000238.	1.3	16
10	Improvement of alkali metal ion batteries <i>via</i> interlayer engineering of anodes: from graphite to graphene. Nanoscale, 2021, 13, 12521-12533.	2.8	14
11	Bilayer Tellurene: A Potential pâ€Type Channel Material for Subâ€10 nm Transistors. Advanced Theory and Simulations, 2021, 4, 2000252.	1.3	14
12	Valley pseudospin in monolayer <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>Mo</mml:mi><mml:msub><mml:mi>Si</mml:mi><mml:m mathvariant="normal">N</mml:mi><mml:mn>4</mml:mn></mml:msub></mml:mrow></mml:math> and <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>Mo</mml:mi><mml:msub><mml:mi>Si</mml:mi><mml:m Physical Review B, 2021, 103, .	1.1	82
13	Performance limit of monolayer MoSi₂N₄ transistors. Journal of Materials Chemistry C, 2021, 9, 14683-14698.	2.7	32
14	Laser ablation of pristine Fe foil for constructing a layer-by-layer SiO₂/Fe₂O₃/Fe integrated anode for high cycling-stability lithium-ion batteries. Physical Chemistry Chemical Physics, 2021, 23, 10365-10376.	1.3	7
15	Two-dimensional materials as a stabilized interphase for the solid-state electrolyte Li₁₀GeP₂S₁₂ in lithium metal batteries. Journal of Materials Chemistry A, 2021, 9, 4810-4821.	5.2	12
16	Van der waals BP/InSe heterojunction for tunneling field-effect transistors. Journal of Materials Science, 2021, 56, 8563-8574.	1.7	13
17	Sub-5 nm Monolayer MoS₂ Transistors toward Low-Power Devices. ACS Applied Electronic Materials, 2021, 3, 1560-1571.	2.0	56
18	Layerâ€Controlled Lowâ€Power Tunneling Transistors Based on SnS Homojunction. Advanced Theory and Simulations, 2021, 4, 2000290.	1.3	6

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19	Schottky barrier heights in two-dimensional field-effect transistors: from theory to experiment. Reports on Progress in Physics, 2021, 84, 056501.	8.1	97
20	Is graphite nanomesh a promising anode for the Na/K-Ions batteries?. Carbon, 2021, 176, 242-252.	5.4	28
21	Layer-Dependent Photoabsorption and Photovoltaic Effects in Two-Dimensional <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:msub><mml:mi>Bi</mml:mi><mml:mn>2</mml:mn></mml:msub><mml:msub><mml:mrow><mml:mrow><m mathvariant="normal">O</mml:mi></mml:mrow></mml:mrow><mml:mn>2</mml:mn></mml:msub><mml:mi>X</mml:mi></mml:ma		

#	ARTICLE	IF	CITATIONS
37	Ohmic contacts of monolayer Tl2O field-effect transistors. Journal of Materials Science, 2020, 55, 11439-11450.	1.7	9
38	First-principles simulation of monolayer hydrogen passivated Bi₂O₂S₂â€“metal interfaces. Physical Chemistry Chemical Physics, 2020, 22, 7853-7863.	1.3	9
39	Sub-5 nm monolayer germanium selenide (GeSe) MOSFETs: towards a high performance and stable device. Nanoscale, 2020, 12, 15443-15452.	2.8	27
40	Ultrahigh Capacity of Monolayer Dumbbell C₄N as a Promising Anode Material for Lithium-Ion Battery. Journal of the Electrochemical Society, 2020, 167, 020538.	1.3	11
41	Two-dimensional single-layer PC6 as promising anode materials for Li-ion batteries: The first-principles calculations study. Applied Surface Science, 2020, 510, 145493.	3.1	35
42	Designing sub-10-nm Metal-Oxide-Semiconductor Field-Effect Transistors via Ballistic Transport and Disparate Effective Mass: The Case of Two-Dimensional <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:mrow><mml:mi>Bi</mml:mi><mml:mi mathvariant="normal">N</mml:mi></mml:mrow></mml:math>. Physical Review Applied, 2020, 13, .	1.5	69
43	Device performance limits and negative capacitance of monolayer GeSe and GeTe tunneling field effect transistors. RSC Advances, 2020, 10, 16071-16078.	1.7	21
44	Holey graphite: A promising anode material with ultrahigh storage for lithium-ion battery. Electrochimica Acta, 2020, 346, 136244.	2.6	49
45	Performance Limit of Monolayer WSe₂ Transistors; Significantly Outperform Their MoS₂ Counterpart. ACS Applied Materials & Interfaces, 2020, 12, 20633-20644.	4.0	39
46	Monolayer Honeycomb Borophene: A Promising Anode Material with a Record Capacity for Lithium-Ion and Sodium-Ion Batteries. Journal of the Electrochemical Society, 2020, 167, 090527.	1.3	28
47	Reexamination of the Schottky Barrier Heights in Monolayer MoS₂ Field-Effect Transistors. ACS Applied Nano Materials, 2019, 2, 4717-4726.	2.4	27
48	Surface-Based Li⁺ Complex Enables Uniform Lithium Deposition for Stable Lithium Metal Anodes. ACS Applied Energy Materials, 2019, 2, 4602-4608.	2.5	32
49	Dendriteâ€Free Lithium Deposition via a Superfilling Mechanism for Highâ€Performance Liâ€Metal Batteries. Advanced Materials, 2019, 31, e1903248.	11.1	106
50	Nitrofullerene, a C₆₀-based Bifunctional Additive with Smoothing and Protecting Effects for Stable Lithium Metal Anode. Nano Letters, 2019, 19, 8780-8786.	4.5	83
51	Computational Study of Ohmic Contact at Bilayer InSe-Metal Interfaces: Implications for Field-Effect Transistors. ACS Applied Nano Materials, 2019, 2, 6898-6908.	2.4	13
52	High-performance sub-10 nm monolayer Bi₂O₂Se transistors. Nanoscale, 2019, 11, 532-540.	2.8	196
53	A sub-10 nm monolayer ReS₂ transistor for low-power applications. Journal of Materials Chemistry C, 2019, 7, 1604-1611.	2.7	32
54	Interfacial Properties of Monolayer Antimonene Devices. Physical Review Applied, 2019, 11, .	1.5	22

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55	Excellent Device Performance of Subâ€5â€nm Monolayer Tellurene Transistors. Advanced Electronic Materials, 2019, 5, 1900226.	2.6	65
56	Monolayer GaS with high ion mobility and capacity as a promising anode battery material. Journal of Materials Chemistry A, 2019, 7, 14042-14050.	5.2	32
57	Directly imaging the structureâ€"property correlation of perovskites in crystalline microwires. Journal of Materials Chemistry A, 2019, 7, 13305-13314.	5.2	9
58	Pervasive Ohmic Contacts in Bilayer Bi₂O₂Seâ€"Metal Interfaces. Journal of Physical Chemistry C, 2019, 123, 8923-8931.	1.5	17
59	Unusual Fermiâ€Level Pinning and Ohmic Contact at Monolayer Bi 2 O 2 Seâ€"Metal Interface. Advanced Theory and Simulations, 2019, 2, 1800178.	1.3	20
60	Schottky Contact in Monolayer WS₂ Fieldâ€Effect Transistors. Advanced Theory and Simulations, 2019, 2, 1900001.	1.3	42
61	Sub 10 nm Bilayer Bi₂O₂Se Transistors. Advanced Electronic Materials, 2019, 5, 1800720.	2.6	70
62	Sub-10 nm tunneling field-effect transistors based on monolayer group IV mono-chalcogenides. Nanoscale, 2019, 11, 23392-23401.	2.8	30
63	Gate-tunable interfacial properties of in-plane ML MX₂ 1Tâ€²â€"2H heterojunctions. Journal of Materials Chemistry C, 2018, 6, 5651-5661.	2.7	54
64	Ohmic contacts between monolayer WSe2 and two-dimensional titanium carbides. Carbon, 2018, 135, 125-133.	5.4	55
65	Direct Observation of Semiconductorâ€"Metal Phase Transition in Bilayer Tungsten Diselenide Induced by Potassium Surface Functionalization. ACS Nano, 2018, 12, 2070-2077.	7.3	44
66	Epitaxial Singleâ€Layer MoS₂ on GaN with Enhanced Valley Helicity. Advanced Materials, 2018, 30, 1703888.	11.1	80
67	Three-layer phosphorene-metal interfaces. Nano Research, 2018, 11, 707-721.	5.8	72
68	Electrical contacts in monolayer blue phosphorene devices. Nano Research, 2018, 11, 1834-1849.	5.8	55
69	Synergism of Rare Earth Trihydrides and Graphite in Lithium Storage: Evidence of Hydrogenâ€Enhanced Lithiation. Advanced Materials, 2018, 30, 1704353.	11.1	25
70	High-performance sub-10-nm monolayer black phosphorene tunneling transistors. Nano Research, 2018, 11, 2658-2668.	5.8	47
71	n-Type Ohmic contact and p-type Schottky contact of monolayer InSe transistors. Physical Chemistry Chemical Physics, 2018, 20, 24641-24651.	1.3	33
72	Sub-5 nm monolayer black phosphorene tunneling transistors. Nanotechnology, 2018, 29, 485202.	1.3	21

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73	n- and p-type ohmic contacts at monolayer gallium nitrideâ€“metal interfaces. Physical Chemistry Chemical Physics, 2018, 20, 24239-24249.	1.3	13
74	Interfacial Properties of Monolayer SnSâ€“Metal Contacts. Journal of Physical Chemistry C, 2018, 122, 12322-12331.	1.5	15
75	Spontaneous valley splitting and valley pseudospin field effect transistors of monolayer VAgP₂Se₆. Nanoscale, 2018, 10, 13986-13993.	2.8	50
76	Monolayer tellureneâ€“metal contacts. Journal of Materials Chemistry C, 2018, 6, 6153-6163.	2.7	81
77	Dependence of excited-state properties of tellurium on dimensionality: From bulk to two dimensions to one dimensions. Physical Review B, 2018, 98, .	1.1	27
78	Simulations of Quantum Transport in Sub-5-nm Monolayer Phosphorene Transistors. Physical Review Applied, 2018, 10, .	1.5	144
79	Sub-5 nm Monolayer Arsenene and Antimonene Transistors. ACS Applied Materials & Interfaces, 2018, 10, 22363-22371.	4.0	77
80	Many-Body Effect and Device Performance Limit of Monolayer InSe. ACS Applied Materials & Interfaces, 2018, 10, 23344-23352.	4.0	98
81	Can a Black Phosphorus Schottky Barrier Transistor Be Good Enough?. ACS Applied Materials & Interfaces, 2017, 9, 3959-3966.	4.0	70
82	Many-body Effect, Carrier Mobility, and Device Performance of Hexagonal Arsenene and Antimonene. Chemistry of Materials, 2017, 29, 2191-2201.	3.2	244
83	Monolayer Bismuthene-Metal Contacts: A Theoretical Study. ACS Applied Materials & Interfaces, 2017, 9, 23128-23140.	4.0	73
84	A computational study of monolayer hexagonal WTe₂ to metal interfaces. Physica Status Solidi (B): Basic Research, 2017, 254, 1600837.	0.7	17
85	Schottky Barriers in Bilayer Phosphorene Transistors. ACS Applied Materials & Interfaces, 2017, 9, 12694-12705.	4.0	94
86	Electronic properties of layered phosphorus heterostructures. Physical Chemistry Chemical Physics, 2017, 19, 1229-1235.	1.3	10
87	Black phosphorus transistors with van der Waals-type electrical contacts. Nanoscale, 2017, 9, 14047-14057.	2.8	76
88	Electrical Contacts in Monolayer Arsenene Devices. ACS Applied Materials & Interfaces, 2017, 9, 29273-29284.	4.0	76
89	Does the Dirac cone of germanene exist on metal substrates?. Physical Chemistry Chemical Physics, 2016, 18, 19451-19456.	1.3	39
90	Origin of the wide band gap from 0.6 to 2.3 eV in photovoltaic material InN: quantum confinement from surface nanostructure. Journal of Materials Chemistry A, 2016, 4, 17412-17418.	5.2	6

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91	Performance Upper Limit of subâ€10 nm Monolayer MoS₂ Transistors. Advanced Electronic Materials, 2016, 2, 1600191.	2.6	97
92	Anomalous Light Emission and Wide Photoluminescence Spectra in Graphene Quantum Dot: Quantum Confinement from Edge Microstructure. Journal of Physical Chemistry Letters, 2016, 7, 2888-2892.	2.1	25
93	Interfacial Properties of Monolayer and Bilayer MoS2 Contacts with Metals: Beyond the Energy Band Calculations. Scientific Reports, 2016, 6, 21786.	1.6	224
94	Interfacial Properties of Monolayer MoSe₂â€“Metal Contacts. Journal of Physical Chemistry C, 2016, 120, 13063-13070.	1.5	70
95	Monolayer Phosphoreneâ€“Metal Contacts. Chemistry of Materials, 2016, 28, 2100-2109.	3.2	199
96	Does p-type ohmic contact exist in WSe₂â€“metal interfaces?. Nanoscale, 2016, 8, 1179-1191.	2.8	166
97	Tunable Valley Polarization and Valley Orbital Magnetic Moment Hall Effect in Honeycomb Systems with Broken Inversion Symmetry. Scientific Reports, 2015, 5, 13906.	1.6	16
98	Phase formations and magnetic properties of single crystal nickel ferrite (NiFe₂O₄) with different morphologies. CrystEngComm, 2015, 17, 1603-1608.	1.3	67
99	Silicene nanomesh. Scientific Reports, 2015, 5, 9075.	1.6	42
100	Origin of 3.45 eV Emission Line and Yellow Luminescence Band in GaN Nanowires: Surface Microwire and Defect. ACS Nano, 2015, 9, 9276-9283.	7.3	43
101	Allâ€Metallic Vertical Transistors Based on Stacked Dirac Materials. Advanced Functional Materials, 2015, 25, 68-77.	7.8	59
102	Quantum spin Hall insulators and quantum valley Hall insulators of BiX/SbX (X=H, F, Cl and Br) monolayers with a record bulk band gap. NPG Asia Materials, 2014, 6, e147-e147.	3.8	242
103	First-principle calculation and assignment for vibrational spectra of Ba(Mg1/3Nb2/3)O3 microwave dielectric ceramic. Journal of Applied Physics, 2014, 115, .	1.1	54
104	Evidence of Type-II Band Alignment in III-nitride Semiconductors: Experimental and theoretical investigation for In0.17Al0.83N/GaN heterostructures. Scientific Reports, 2014, 4, 6521.	1.6	23
105	Does the Dirac Cone Exist in Silicene on Metal Substrates?. Scientific Reports, 2014, 4, 5476.	1.6	92
106	Tunable band gap in few-layer graphene by surface adsorption. Scientific Reports, 2013, 3, .	1.6	55
107	Adsorption configurations of carbon monoxide on gold monolayer supported by graphene or monolayer hexagonal boron nitride: a first-principles study. European Physical Journal B, 2013, 86, 1.	0.6	6
108	Structural, Electronic, and Optical Properties of Bulk Graphdiyne. Journal of Physical Chemistry C, 2013, 117, 13072-13079.	1.5	101

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109	Enhanced manyâ€body effects in oneâ€dimensional linear atomic chains. Physica Status Solidi (B): Basic Research, 2013, 250, 1636-1643.	0.7	7
110	Firstâ€Principle Calculation and Assignment for Vibrational Spectra of <scp><scp>Ba</scp></scp>(<scp><scp>Mg</scp></scp>_{1/2}<scp><scp>W</scp></scp>_{1/2})<scp><scp>O</ Microwave Dielectric Ceramic. Journal of the American Ceramic Society, 2013, 96, 2898-2905.	1.9	63
111	Electronic structures and properties of lanthanide hexaboride nanowires. Journal of Applied Physics, 2013, 114, 143709.	1.1	5
112	INTERACTION OF SINGLE-WALLED CARBON NANOTUBES WITH AMINE. Nano, 2012, 07, 1130001.	0.5	15
113	Electron transport through single endohedral Ce@C<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mn>82</mml:mn></mml:msub></mml:math>metallofullerenes. Physical Review B, 2012, 86, .	1.1	35
114	High performance silicene nanoribbon field effect transistors with current saturation. European Physical Journal B, 2012, 85, 1.	0.6	48
115	Tunable and sizable band gap of single-layer graphene sandwiched between hexagonal boron nitride. NPG Asia Materials, 2012, 4, e6-e6.	3.8	158
116	Tunable and sizable band gap in silicene by surface adsorption. Scientific Reports, 2012, 2, 853.	1.6	253
117	Electrically controlled electron transfer and resistance switching in reduced graphene oxide noncovalently functionalized with thionine. Journal of Materials Chemistry, 2012, 22, 16422.	6.7	42
118	Structure and Electronic and Transport Properties of Transition Metal Intercalated Graphene and Graphene-Hexagonal-Boron-Nitride Bilayer. Journal of Physical Chemistry C, 2011, 115, 25273-25280.	1.5	23
119	Electric-Field-Induced Energy Gap in Few-Layer Graphene. Journal of Physical Chemistry C, 2011, 115, 9458-9464.	1.5	72
120	Negative differential resistance in parallel single-walled carbon nanotube contacts. Physical Review B, 2011, 83, .	1.1	31
121	Quasiparticle energies and excitonic effects of the two-dimensional carbon allotrope graphdiyne: Theory and experiment. Physical Review B, 2011, 84, .	1.1	305
122	Ultra-narrow WS₂nanoribbons encapsulated in carbon nanotubes. Journal of Materials Chemistry, 2011, 21, 171-180.	6.7	74
123	Negative rectification and negative differential resistance in nanoscale single-walled carbon nanotube p-n junctions. Theoretical Chemistry Accounts, 2011, 130, 353-359.	0.5	10
124	Tuning graphene nanoribbon field effect transistors via controlling doping level. Theoretical Chemistry Accounts, 2011, 130, 483-489.	0.5	5
125	Gd-doping effect on performance of HfO2 based resistive switching memory devices using implantation approach. Applied Physics Letters, 2011, 98, .	1.5	165
126	Selection of single-walled carbon nanotubes according to both their diameter and chirality via nanotweezers. Nano Research, 2010, 3, 296-306.	5.8	13

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127	Electron localization and emission mechanism in wurtzite (Al, In, Ga)N alloys. Physica Status Solidi (B): Basic Research, 2010, 247, 109-114.	0.7	14
128	Separation of metallic singleâ€walled carbon nanotubes using various amines. Physica Status Solidi (B): Basic Research, 2010, 247, 2641-2644.	0.7	25
129	Room-temperature giant magnetoresistance over one billion percent in a bare graphene nanoribbon device. Physical Review B, 2010, 81, .	1.1	44
130	Ionic doping effect in ZrO2 resistive switching memory. Applied Physics Letters, 2010, 96, .	1.5	154
131	Magnetism in carbon nanoscrolls: Quasi-half-metals and half-metals in pristine hydrocarbons. Nano Research, 2009, 2, 844-850.	5.8	11
132	XRD and Raman Studies on the Ordering/Disordering of Ba(Mg_{1/3}Ta_{2/3})O₃. Journal of the American Ceramic Society, 2009, 92, 1547-1551.	1.9	82
133	Magnetic Properties of Fully Bare and Half-Bare Boron Nitride Nanoribbons. Journal of Physical Chemistry C, 2009, 113, 2273-2276.	1.5	102
134	Assignment of Raman-active vibrational modes of MgTiO3. Journal of Applied Physics, 2008, 104, .	1.1	49
135	Preparation of transparent and conductive thin films of metallic single-walled carbon nanotubes. Journal of Materials Chemistry, 2008, 18, 4189.	6.7	21
136	First-Principles Calculation of ¹³C NMR Chemical Shifts of Infinite Single-Walled Carbon Nanotubes: New Data for Large-Diameter and Four-Helical Nanotubes. Journal of Physical Chemistry C, 2008, 112, 16417-16421.	1.5	18
137	Far infrared reflection spectrum and IR-active modes of MgTiO3. Journal of Applied Physics, 2008, 103, 074105.	1.1	16
138	STRUCTURAL AND ELECTRONIC PROPERTIES OF ONE DIMENSIONAL KxC60 CRYSTAL ENCAPSULATED IN CARBON NANOTUBE. International Journal of Modern Physics B, 2007, 21, 1705-1714.	1.0	4
139	First-principles study of hydrogen-passivated single-crystalline silicon nanotubes: electronic and optical properties. Nanotechnology, 2007, 18, 505707.	1.3	17
140	EXTRACTION OF METALLIC NANOTUBES OF ZEOLITE-SUPPORTED SINGLE-WALLED CARBON NANOTUBES SYNTHESIZED FROM ALCOHOL. Nano, 2007, 02, 221-226.	0.5	7
141	Static and Optical Transverse and Longitudinal Screened Polarizabilities of Boron Nitride Nanotubes. Journal of Physical Chemistry C, 2007, 111, 3285-3289.	1.5	17
142	Why Semiconducting Singleâ€Walled Carbon Nanotubes are Separated from their Metallic Counterparts. Small, 2007, 3, 1566-1576.	5.2	68
143	Evolution of the Electronic Properties of Metallic Single-Walled Carbon Nanotubes with the Degree of CCl2Covalent Functionalization. Journal of Physical Chemistry B, 2006, 110, 5655-5658.	1.2	21
144	Selective Interaction of Large or Charge-Transfer Aromatic Molecules with Metallic Single-Wall Carbon Nanotubes:Â Critical Role of the Molecular Size and Orientation. Journal of the American Chemical Society, 2006, 128, 5114-5118.	6.6	168

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145	Interplay of single-wall carbon nanotubes and encapsulatedLa@C82,La2@C80, andSc3N@C80. Physical Review B, 2005, 71, .	1.1	18
146	Structural and electronic properties of heterofullerene C59P. Molecular Physics, 2001, 99, 1203-1207.	0.8	22
147	Structural and electronic properties of endohedral phosphorus fullerene P@C60: an off-centre displacement of P inside the cage. Molecular Physics, 2001, 99, 1199-1202.	0.8	7
148	Application of the Recursion Method to the Electronic Structures of Simple-Cubic Na2CsC60 and Body-Centered-Cubic K6C60. Modern Physics Letters B, 1997, 11, 659-665.	1.0	2
149	EFFECTS OF ORIENTATION ON THE ELECTRONIC STRUCTURE OF K3C60. Modern Physics Letters B, 1996, 10, 1417-1422.	1.0	6
150	TWO-COMPONENT SUPERCONDUCTIVITY FOR DOPED FULLERENES. Modern Physics Letters B, 1996, 10, 823-829.	1.0	2
151	NUMERICAL APPLICATION OF THE RECURSION METHOD TO THE ELECTRONIC STRUCTURE OF C60. Modern Physics Letters B, 1996, 10, 1133-1139.	1.0	1
152	Device performance limit of monolayer SnSe2 MOSFET. Nano Research, 0, , 1.	5.8	9
153	Tunable and sizable band gap in silicene by surface adsorption. , 0, .		1